

69

PJQ5858A-AU

60V Dual N-Channel Enhancement Mode MOSFET

Current

16 A

Voltage

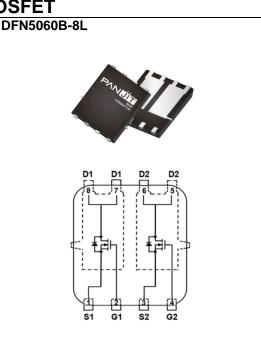
ge 60 V

Features

- Rds(on), Vgs@10V, Id@8A<50mΩ
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@4A < 60m\Omega$
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN5060B-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.092 grams



Maximum Ratings and Thermal Characteristics (TA=25°C unless otherwise noted)

PARAMETE	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage		V _{DS}	60		
Gate-Source Voltage		V _{GS}	±20		
Continuous Drain Current ^(Note 3)	T _C =25°C		16		
	Tc=100°C	I _D	12	A	
Pulsed Drain Current(Note 1)	T _c =25°C	I _{DM}	64		
Power Dissipation	T _c =25°C	5	25	14/	
	Tc=100°C	PD	12.5	W	
Continuous Drain Current ^(Note 4)	T _A =25°C		5		
	T _A =70°C	I _D	4.5	Α	
Power Dissipation	T _A =25°C	D-	2.5	W	
	T _A =70°C	PD	1.8	VV	
Single Pulse Avalanche Energy ^(Note 5)		Eas	1.6	mJ	
Operating Junction and Storage Temperature Range		TJ,TSTG	-55~175	°C	
Thermal Resistance ^(Note 4)	Junction to Case	$R_{ extsf{ heta}JC}$	6	°C/W	
	Junction to Ambient	R _{θJA}	60	C/W	



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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	60	-	-	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1	1.7	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =8A	-	34	50	mΩ
		V _{GS} =4.5V, I _D =4A	-	38	60	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =60V, V_{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Dynamic ^(Note 6)						
Total Gate Charge	Qg	V _{DS} =48V, I _D =8A, V _{GS} =10V	-	13	-	nC
Gate-Source Charge	Qgs		-	2.1	-	
Gate-Drain Charge	Q _{gd}		-	2.9	-	
Input Capacitance	Ciss	V _{DS} =30V, V _{GS} =0V, f=1MHz	-	609	-	pF
Output Capacitance	Coss		-	43	-	
Reverse Transfer Capacitance	Crss		-	14	-	
Gate resistance	Rg	f=1MHz	-	3.7	-	Ω
Turn-On Delay Time	td _(on)	V _{DS} =48V, I _D =8A, V _{GS} =10V, R _G =3Ω (Note 2,3)	-	8.4	-	ns
Turn-On Rise Time	tr		-	33	-	
Turn-Off Delay Time	td(off)		-	32	-	
Turn-Off Fall Time	tf		-	27	-	
Drain-Source Diode		·				
Diode Forward Current	Is	Tc=25°C	-	-	16	A
Pulsed Diode Forward Current	I _{SM}		-	-	64	
Diode Forward Voltage	V _{SD}	Is=1A, V _{GS} =0V	-	0.72	1	V
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =8A	-	25	-	ns
Reverse Recovery Charge	Qrr	dls/dt=100A/us	-	12	-	nC

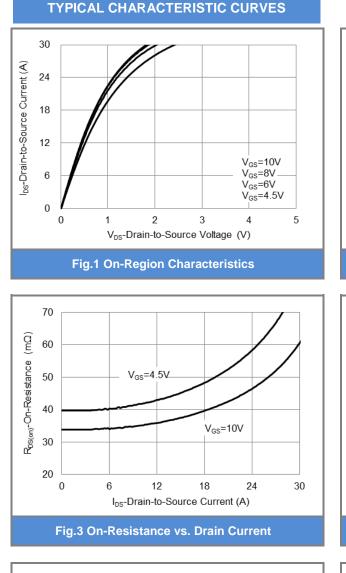
NOTES :

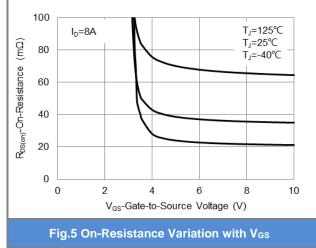
- 1. Pulse width100us, Duty cycle<2%.</td>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an $R_{\theta JC}$ = 6°C/W.
- 4. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.1mH, I_{AS}=5.6A, V_{DD}=30V, V_{GS}=10V, Starting T_J=25^{\circ}C.
- 6. Guaranteed by design, not subject to production testing.

SEMI CONDUCTOR

PANJ

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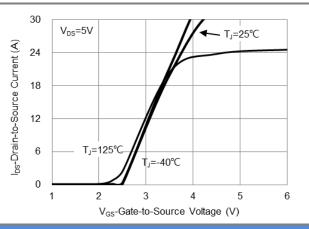


Fig.2 Transfer Characteristics

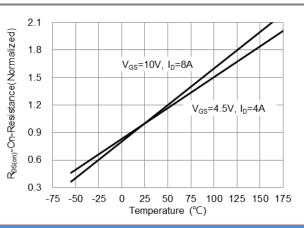
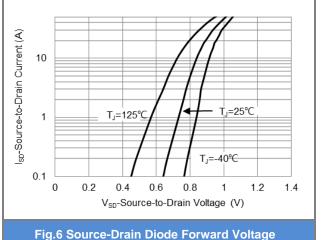


Fig.4 On-Resistance vs. Junction temperature

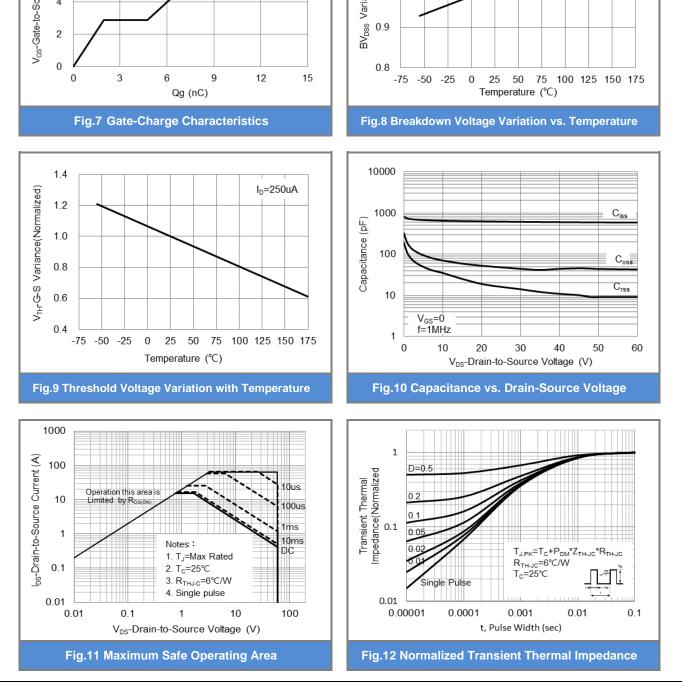


March 3,2023

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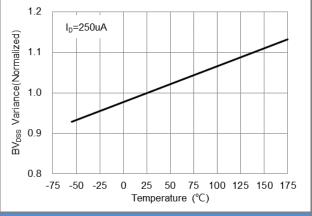


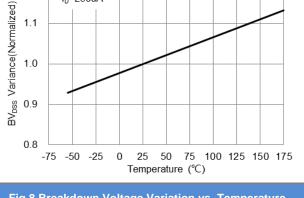


TYPICAL CHARACTERISTIC CURVES

PJQ5858A-AU

10 V_{DS}=48V I_D=8A V_{GS}-Gate-to-Source Voltage (V) 8 6 4





PANJ SEM CONDUCTOR



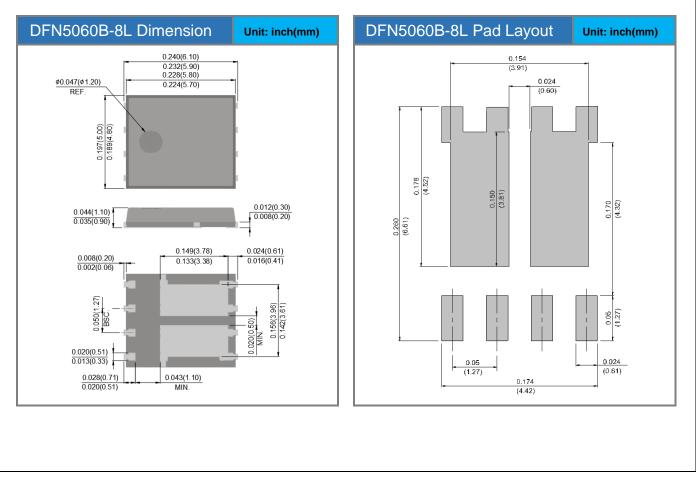


PJQ5858A-AU

Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ5858A-AU_R2_000A1	DFN5060B-8L	3K pcs / 13" reel	Q5858A	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout



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